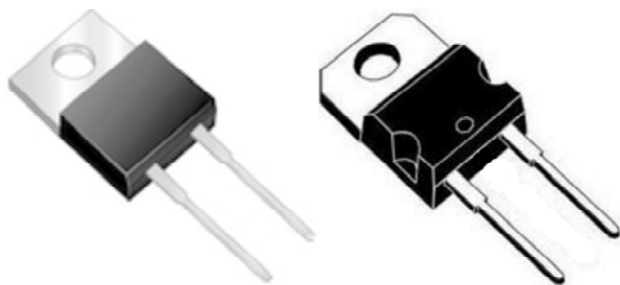
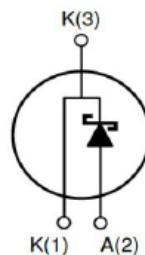


**ESIC04065S****Silicon carbide power schottky diode****TO-220AC****Internal Schematic**

Features
• Rated to 650V at 4 Amps • Zero reverse recovery current • Zero forward recovery voltage • Temperature independent switching behaviour • High temperature operation • High frequency operation • Marking : ESIC04065S

Benefits
• Unipolar rectifier • Substantially reduced switching losses • No thermal run-away with parallel devices • Reduced heat sink requirements

Ordering Information		
Part No.	Package	Packing
ESIC04065S	TO-220AC	50 / Tube

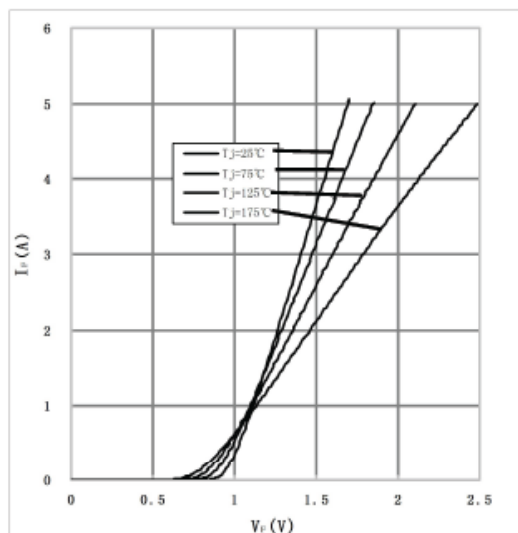
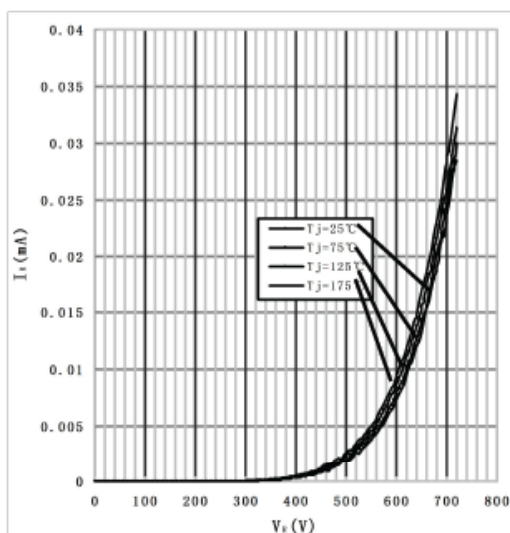
Application
• SMPS, e.g., CCM PFC • Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)				
Parameter	Symbol	Conditions	Limit	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_J=25^{\circ}\text{C}$	650	V
Surge Peak Reverse Voltage	V_{RSM}	$T_J=25^{\circ}\text{C}$	650	V
DC Blocking Voltage	V_{DC}	$T_J=25^{\circ}\text{C}$	650	V
Continuous Forward Current	I_F	$T_C=25^{\circ}\text{C}$	11	A
		$T_C=135^{\circ}\text{C}$	5	
		$T_C=150^{\circ}\text{C}$	4	
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Wave, $D=0.3$	15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	30	A
Power Dissipation	P_{TOT}	$T_C=25^{\circ}\text{C}$	53.2	W
		$T_C=110^{\circ}\text{C}$	30	
Operating Junction and Storage Temperature	T_J , T_{stg}		-55~+175	$^{\circ}\text{C}$
Typical Thermal Resistance from Junction to Case	$R_{\theta JC}$		2.82	$^{\circ}\text{C/W}$

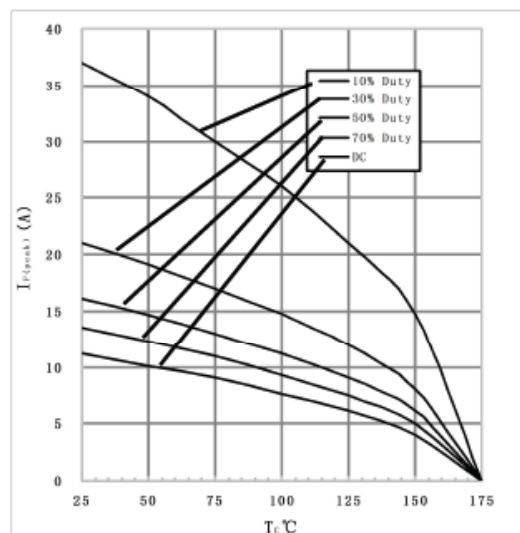
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage	$I_F=4\text{A}, T_J=25^\circ\text{C}$	V_F	-	1.55	1.7	V
	$I_F=4\text{A}, T_J=175^\circ\text{C}$		-	2.2	2.5	
Reverse Current	$V_R=650\text{V}, T_J=25^\circ\text{C}$	I_R	-	10	100	μA
	$V_R=650\text{V}, T_J=175^\circ\text{C}$		-	20	200	
Total Capacitive Charge	$V_R=400\text{V}, T_J=150^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$	Q_C	-	11	-	nC
Total Capacitive Charge	$V_R=0\text{V}, T_J=25^\circ\text{C}, f=1\text{MHz}$	C	-	181	220	pF
	$V_R=200\text{V}, T_J=25^\circ\text{C}, f=1\text{MHz}$		-	22.5	25	
	$V_R=400\text{V}, T_J=25^\circ\text{C}, f=1\text{MHz}$		-	20.5	21	

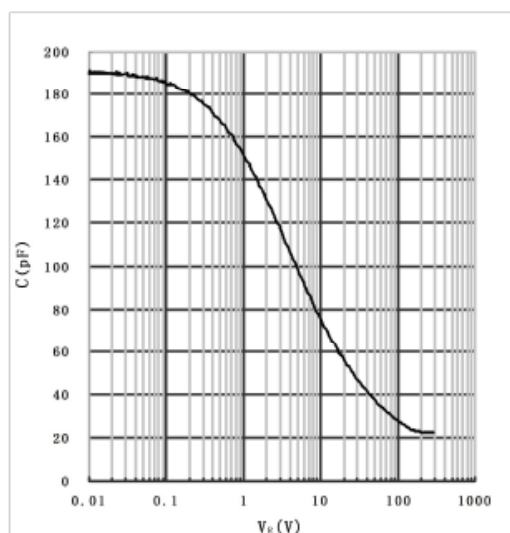
Rating and Characteristics Curves

1) Forward IV characteristics as a function of T_J :2) Reverse IV characteristics as a function of T_J :

3) Current Derating



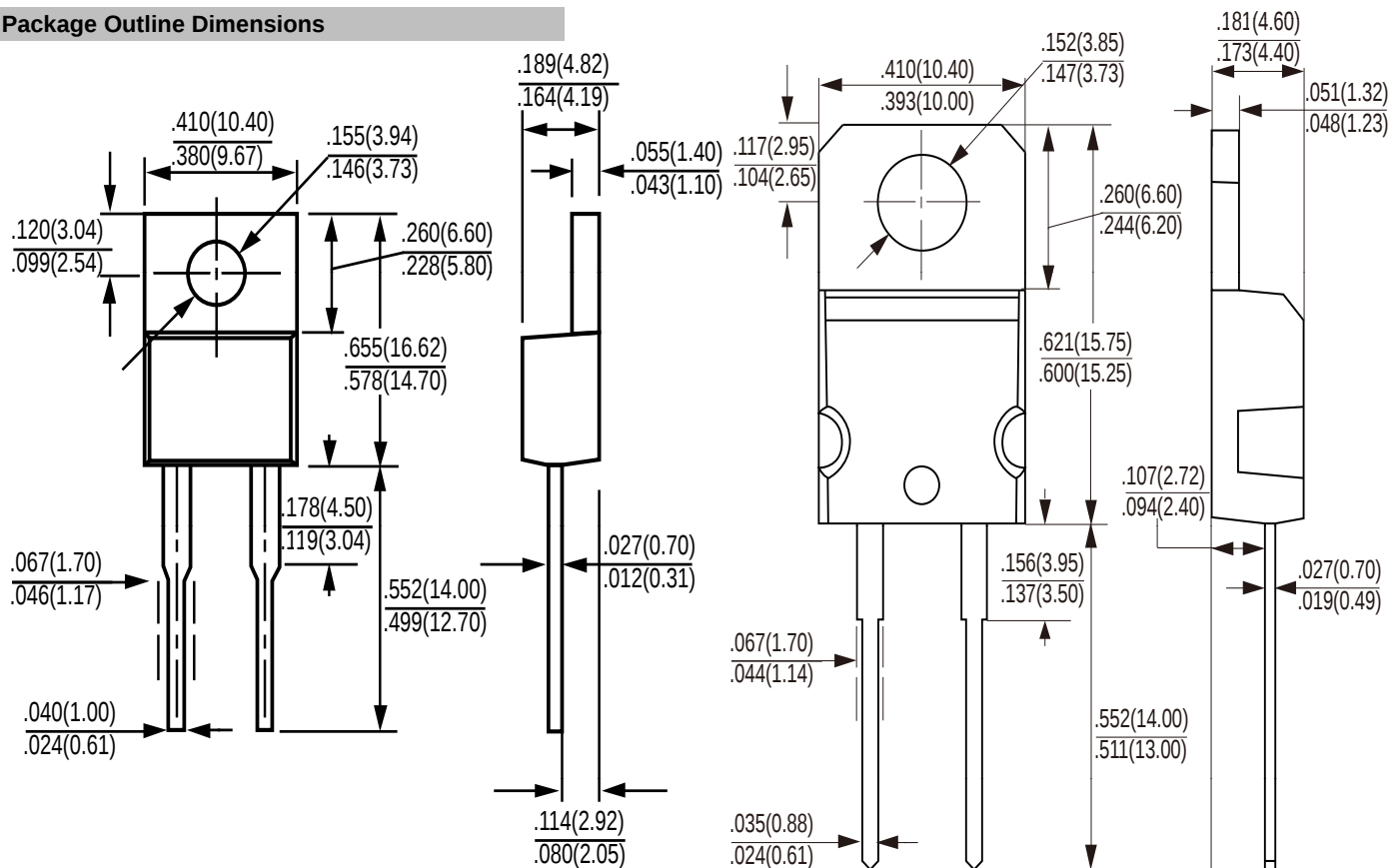
4) Capacitance vs. reverse voltage :





Silicon carbide power schottky diode

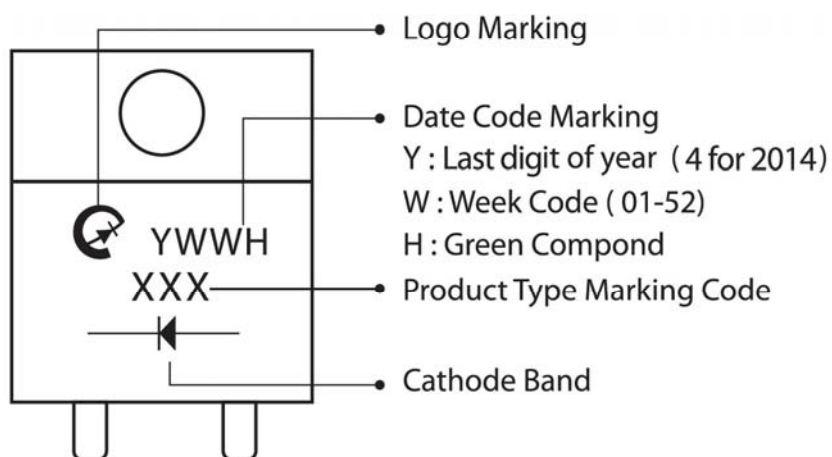
Package Outline Dimensions



TO-220AC

Dimensions in inches and (millimeters)

Marking Information



Bulk Packing

Package	Inner Pack	Inner Box (EA)	Inner Box (mm)	Carton (EA)	Carton Size (mm)	Gross Weight (Kg)-Approx.
TO-220AC	Tube	2000	539x184x79	4000	558x180x200	11.9